

	Hits	Search Text	DBs
1	301	((metal\$4 or film or dielectric or ((under or bottom) near8 (layer or film or coat\$3))) same (photoresist or resist or photo\$4cur\$4 or photo\$3imageable) same (novolac or epoxy or resin) same (((photoactive or photo\$4acid) near7 (generat\$4 or liberat\$4)) or PAG or (acid near8 (generat\$4 or liberat\$4))) same (expos\$4 or illuminat\$4 or irradiat\$4)) and develop\$4 and ((solubilization or solubilizing or soluble or solubility or insoluble) same (prevent\$4 or caus\$4 or inhibit\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
2	120	((metal\$4 or film or dielectric or ((under or bottom) near8 (layer or film or coat\$3))) same (photoresist or resist or photo\$4cur\$4 or photo\$3imageable) same (novolac or epoxy or resin) same (((photoactive or photo\$4acid) near7 (generat\$4 or liberat\$4)) or PAG or (acid near8 (generat\$4 or liberat\$4))) same (expos\$4 or illuminat\$4 or irradiat\$4)) and develop\$4 and ((solubilization or solubilizing or soluble or solubility or insoluble) same (prevent\$4 or caus\$4 or inhibit\$4)) and polyhydroxystyrene	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
3	1	((metal\$4 or film or dielectric or ((under or bottom) near8 (layer or film or coat\$3))) same (photoresist or resist or photo\$4cur\$4 or photo\$3imageable) same (novolac or epoxy or resin) same (((photoactive or photo\$4acid) near7 (generat\$4 or liberat\$4)) or PAG or (acid near8 (generat\$4 or liberat\$4)))) same (expos\$4 or illuminat\$4 or irradiat\$4) same ((upper or top) near9 (layer or coat\$4 or film))) and develop\$4 and ((solubilization or solubilizing or soluble or solubility or insoluble) same (prevent\$4 or caus\$4 or inhibit\$4)) and polyhydroxystyrene	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
4	182	430/270.1.ccls. and ((metal\$4 or film or dielectric or ((under or bottom) near8 (layer or film or coat\$3))) same (photoresist or resist or photo\$4cur\$4 or photo\$3imageable) same (novolac or epoxy or resin) same (((photoactive or photo\$4acid) near7 (generat\$4 or liberat\$4)) or PAG or (acid near8 (generat\$4 or liberat\$4)))) same (expos\$4 or illuminat\$4 or irradiat\$4)) and develop\$4 and ((solubilization or solubilizing or soluble or solubility or insoluble) same (prevent\$4 or caus\$4 or inhibit\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
5	2	((metal\$4 or dielectric or ((under or bottom or conductive) near14 (layer or film or coat\$3))) same (photoresist or resist or photo\$4cur\$4 or photo\$3imageable) same (novolac or epoxy or resin) same (((photoactive or photo\$4acid) near7 (generat\$4 or liberat\$4)) or PAG or (acid near8 (generat\$4 or liberat\$4))) same (expos\$4 or illuminat\$4 or irradiat\$4) same ((upper or top or outer or protective or mask or pattern\$3) near9 (layer or coat\$4 or film))) and develop\$4 and (solubilization or \$3solubilizing or soluble or solubility or insoluble) and polyhydroxystyrene	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
6	128	((under or bottom or conductive or metal\$4 or dielectric) near14 (deposit\$4 or form\$3 or layer or film or coat\$3)) and ((photoresist or resist or photo\$4cur\$4 or photo\$3imageable) same (novolac or epoxy or resin\$3) same (((photoactive or photo\$4acid) near7 (generat\$4 or liberat\$4)) or PAG or (acid near8 (generat\$4 or liberat\$4))) same (expos\$4 or illuminat\$4 or irradiat\$4) same pattern\$4) and develop\$4 and ((solubilization or \$3solubilizing or soluble or solubility or insoluble) same (prevent\$4 or caus\$4 or inhibit\$4)) and polyhydroxystyrene	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
7	0	((under or bottom or conductive or metal\$4 or dielectric) near14 (deposit\$4 or form\$3 or layer or film or coat\$3)) and ((photoresist or resist or photo\$4cur\$4 or photo\$3imageable) same (novolac or epoxy or resin\$3) same (((photoactive or photo\$4acid) near7 (generat\$4 or liberat\$4)) or PAG or (acid near8 (generat\$4 or liberat\$4))) same (expos\$4 or illuminat\$4 or irradiat\$4) same pattern\$4) and develop\$4 and ((solubilization or \$3solubilizing or soluble or solubility or insoluble) same (prevent\$4 or caus\$4 or inhibit\$4)) and polyhydroxystyrene and ((CD or (critical near5 dimension)) same etch\$4 same (feature or lines or contact) same (LER or LWR or (line near4 (wid\$2 or edge) near4 rough\$5)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
8	0	((under or bottom or conductive or metal\$4 or dielectric) near14 (deposit\$4 or form\$3 or layer or film or coat\$3)) and ((photoresist or resist or photo\$4cur\$4 or photo\$3imageable) same (novolac or epoxy or resin\$3) same (((photoactive or photo\$4acid) near7 (generat\$4 or liberat\$4)) or PAG or (acid near8 (generat\$4 or liberat\$4))) same (expos\$4 or illuminat\$4 or irradiat\$4) same pattern\$4) and develop\$4 and ((solubilization or \$3solubilizing or soluble or solubility or insoluble) same (prevent\$4 or caus\$4 or inhibit\$4)) and polyhydroxystyrene and ((CD or (critical near5 dimension)) same (feature or lines or contact) same (LER or LWR or (line near4 (wid\$2 or edge) near4 rough\$5))) and (etch\$4 or RIE or (dry near5 etch\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
9	3	((under or bottom or conductive or metal\$4 or dielectric) near14 (deposit\$4 or form\$3 or layer or film or coat\$3)) and ((photoresist or resist or photo\$4cur\$4 or photo\$3imageable) same (novolac or epoxy or resin\$3) same (((photoactive or photo\$4acid) near7 (generat\$4 or liberat\$4)) or PAG or (acid near8 (generat\$4 or liberat\$4))) same (expos\$4 or illuminat\$4 or irradiat\$4) same pattern\$4) and develop\$4 and ((solubilization or \$3solubilizing or soluble or solubility or insoluble) same (prevent\$4 or caus\$4 or inhibit\$4)) and polyhydroxystyrene and ((CD or (critical near5 dimension)) same (feature or lines or contact)) and (LER or LWR or (line near4 (wid\$2 or edge) near4 rough\$5)) and (etch\$4 or RIE or (dry near5 etch\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
10	0	(((under or bottom or conductive or metal\$4 or dielectric) near14 (deposit\$4 or form\$3 or layer or film or coat\$3)) same pattern\$4) and ((photoresist or resist or photo\$4cur\$4 or photo\$3imageable) same (novolac or epoxy or resin\$3) same (((photoactive or photo\$4acid) near7 (generat\$4 or liberat\$4)) or PAG or (acid near8 (generat\$4 or liberat\$4))) same (expos\$4 or illuminat\$4 or irradiat\$4) same pattern\$4) and develop\$4 and ((solubilization or \$3solubilizing or soluble or solubility or insoluble) same (prevent\$4 or caus\$4 or inhibit\$4)) and polyhydroxystyrene and (CD or (critical near5 dimension)) and (LER or LWR or (line near4 (wid\$2 or edge) near4 rough\$5)) and (etch\$4 or RIE or (dry near5 etch\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
11	8	((under or bottom or conductive or metal\$4 or dielectric) near14 (deposit\$4 or form\$3 or layer or film or coat\$3)) and ((photoresist or resist or photo\$4cur\$4 or photo\$3imageable) same (novolac or epoxy or resin\$3) same (vinyl near9 phen\$3) same (((photoactive or photo\$4acid) near7 (generat\$4 or liberat\$4)) or PAG or (acid near8 (generat\$4 or liberat\$4))) same (expos\$4 or illuminat\$4 or irradiat\$4) same pattern\$4) and develop\$4 and ((solubilization or \$3solubilizing or soluble or solubility or insoluble) same (prevent\$4 or caus\$4 or inhibit\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
12	194	((under or bottom or conductive or metal\$4 or dielectric) near14 (deposit\$4 or form\$3 or layer or film or coat\$3)) same pattern\$4) and ((photoresist or resist or photo\$4cur\$4 or photo\$3imageable) same (novolac or epoxy or resin\$3) same (((photoactive or photo\$4acid) near7 (generat\$4 or liberat\$4)) or PAG or (acid near8 (generat\$4 or liberat\$4))) same (expos\$4 or illuminat\$4 or irradiat\$4) same pattern\$4) and develop\$4 and ((solubilization or \$3solubilizing or soluble or solubility or insoluble) same (prevent\$4 or caus\$4 or inhibit\$4)) and (etch\$4 or RIE or (dry near5 etch\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB



	Hits	Search Text	DBs
13	24	(((under or bottom or conductive or metal\$4 or dielectric) near14 (deposit\$4 or form\$3 or layer or film or coat\$3)) same pattern\$4) and ((photoresist or resist or photo\$4cur\$4 or photo\$3imageable) same (novolac or epoxy or resin\$3) same (((photoactive or photo\$4acid) near7 (generat\$4 or liberat\$4)) or PAG or (acid near8 (generat\$4 or liberat\$4))) same (expos\$4 or illuminat\$4 or irradiat\$4) same pattern\$4) and develop\$4 and ((solubilization or \$3solubilizing or soluble or solubility or insoluble) same (prevent\$4 or caus\$4 or inhibit\$4)) and (etch\$4 or RIE or (dry near5 etch\$4)) and (vinyl near9 phenol) and \$4hydroxy\$3styrene	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
14	11	(((under or bottom or conductive or metal\$4 or dielectric) near14 (deposit\$4 or form\$3 or layer or film or coat\$3)) same pattern\$4) and ((photoresist or resist or photo\$4cur\$4 or photo\$3imageable) same (((photoactive or photo\$4acid) near7 (generat\$4 or liberat\$4)) or PAG or (acid near8 (generat\$4 or liberat\$4))) same (expos\$4 or illuminat\$4 or irradiat\$4) same pattern\$4) and develop\$4 and (etch\$4 or RIE or (dry near5 etch\$4)) and ((CD or (critical near5 dimension)) same (feature or line or contact)) and (LER or LWR or (line near4 (wid\$2 or edge) near4 rough\$5))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
15	23	((under or bottom or conductive or metal\$4 or dielectric) near14 (deposit\$4 or form\$3 or layer or film or coat\$3)) same pattern\$4) and ((photoresist or resist or photo\$4cur\$4 or photo\$3imageable) same (expos\$4 or illuminat\$4 or irradiat\$4) same (EUV or (KrF near5 (light or laser)) or excimer) same pattern\$4) and develop\$4 and (etch\$4 or RIE or (dry near5 etch\$4)) and (CD or (critical near5 dimension)) and (LER or LWR or (line near4 (wid\$2 or edge) near4 rough\$5)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
16	0	((under or bottom or conductive or metal\$4 or dielectric) near14 (deposit\$4 or form\$3 or layer or film or coat\$3)) same pattern\$4 same (substrate or wafer or device) same (pedestal or stage or hold\$3)) and ((photoresist or resist or photo\$4cur\$4 or photo\$3imageable) same (expos\$4 or illuminat\$4 or irradiat\$4) same pattern\$4) and develop\$4 and (etch\$4 or RIE or (dry near5 etch\$4)) and (CD or (critical near5 dimension)) and ((LER or LWR or (line near4 (wid\$2 or edge) near4 rough\$5)) same (nm or nanometer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
17	0	((under or bottom or conductive or metal\$4 or dielectric) near14 (deposit\$4 or form\$3 or layer or film or coat\$3)) same pattern\$4 same (substrate or wafer or device) same (pedestal or stage or hold\$3)) and ((photoresist or resist or photo\$4cur\$4 or photo\$3imageable) same (expos\$4 or illuminat\$4 or irradiat\$4) same pattern\$4) and develop\$4 and (etch\$4 or RIE or (dry near5 etch\$4)) and (CD or (critical near5 dimension)) and (LER or LWR or (line near4 (wid\$2 or edge) near4 rough\$5))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
18	2	((under or bottom or conductive or metal\$4 or dielectric) near14 (deposit\$4 or form\$3 or layer or film or coat\$3)) same pattern\$4) and ((photoresist or resist or photo\$4cur\$4 or photo\$3imageable) same (substrate or wafer or device) same (pedestal or stage or hold\$3) same (expos\$4 or illuminat\$4 or irradiat\$4) same pattern\$4) and develop\$4 and (etch\$4 or RIE or (dry near5 etch\$4)) and (CD or (critical near5 dimension)) and (LER or LWR or (line near4 (wid\$2 or edge) near4 rough\$5))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
19	34	((under or bottom or conductive or metal\$4 or dielectric) near14 (deposit\$4 or form\$3 or layer or film or coat\$3)) and ((photoresist or resist or photo\$4cur\$4 or photo\$3imageable) same (expos\$4 or illuminat\$4 or irradiat\$4) same pattern\$4) and develop\$4 and (etch\$4 or RIE or (dry near5 etch\$4)) and ((CD or (critical near5 dimension)) same (nm or nanometer)) and ((LER or LWR or (line near4 (wid\$2 or edge) near4 rough\$5)) same (nm or nanometer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
20	19	((under or bottom or conductive or metal\$4 or dielectric) near14 (deposit\$4 or form\$3 or layer or film or coat\$3)) same pattern\$4) and ((photoresist or resist or photo\$4cur\$4 or photo\$3imageable) same (novolac or epoxy or resin\$3) same vinyl same (((photoactive or photo\$4acid) near7 (generat\$4 or liberat\$4)) or PAG or (acid near8 (generat\$4 or liberat\$4))) same (expos\$4 or illuminat\$4 or irradiat\$4) same pattern\$4) and develop\$4 and ((solubilization or \$3solubilizing or soluble or solubility or insoluble) same (prevent\$4 or caus\$4 or inhibit\$4)) and (etch\$4 or RIE or (dry near5 etch\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
21	36	((bottom or conductive or metal\$4 or dielectric or circuit\$4) near14 (deposit\$4 or form\$3 or layer or film or coat\$3)) and ((photoresist or resist or photo\$4cur\$4 or photo\$3imageable) same (expos\$4 or illuminat\$4 or irradiat\$4) same pattern\$4) and develop\$4 and ((CD or (critical near5 dimension)) same (nm or nanometer)) and ((LER or LWR or (line near4 (wid\$2 or edge) near4 rough\$5)) same (nm or nanometer)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
22	15	((bottom or conductive or metal\$4 or dielectric or circuit\$4) near14 (deposit\$4 or form\$3 or layer or film or coat\$3)) and (photolithograph\$6) and develop\$4 and ((CD or (critical near5 dimension)) same (nm or nanometer)) and ((LER or LWR or (line near4 (wid\$2 or edge) near4 rough\$5)) same (nm or nanometer)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB